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TRANSISTORS, HIGH POWER, NPN

BASED ON TYPE 2N5664, 2N5665, 2N5666 AND 2N5667

ESCC Detail Specification No. 5203/038

as applicable

Issue 2 3 - Draft A	April 2008
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as applicable

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DCR No.	CHANGE DESCRIPTION
329	Specification up issued to incorporate editorial and technical changes per DCR.

tbd

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Collector-Base Voltage Variants 01, 02, 05, 06, 09, 10 Variants 03, 04, 11	V_{CBO}	250 400	V	Over T_{op}
Collector-Emitter Voltage Variants 01, 02, 05, 06, 09, 10 Variants 03, 04, 11	V_{CEO}	200 300	V	Over T_{op} Note 2
Emitter-Base Voltage	V_{EBO}	6	V	Over T_{op}
Collector Current	I_C	5	A	Continuous Note 2
Base Current	I_B	1	A	Continuous
Power Dissipation For TO-66 For TQ-5 and TO-39	P_{tot}	30 15	W	At $T_{case} < +100^{\circ}C$ Note 1
Operating Temperature Range	T_{op}	-65 to +200	$^{\circ}C$	Note 1
Storage Temperature Range	T_{stg}	-65 to +200	$^{\circ}C$	Note 1
Soldering Temperature	T_{sol}	+260	$^{\circ}C$	Note 3
Thermal Resistance Junction to Case For TO-66 For TO-5 and TQ-39	$R_{th(j-c)}$	3.3 6.7	$^{\circ}C/W$	

See attached

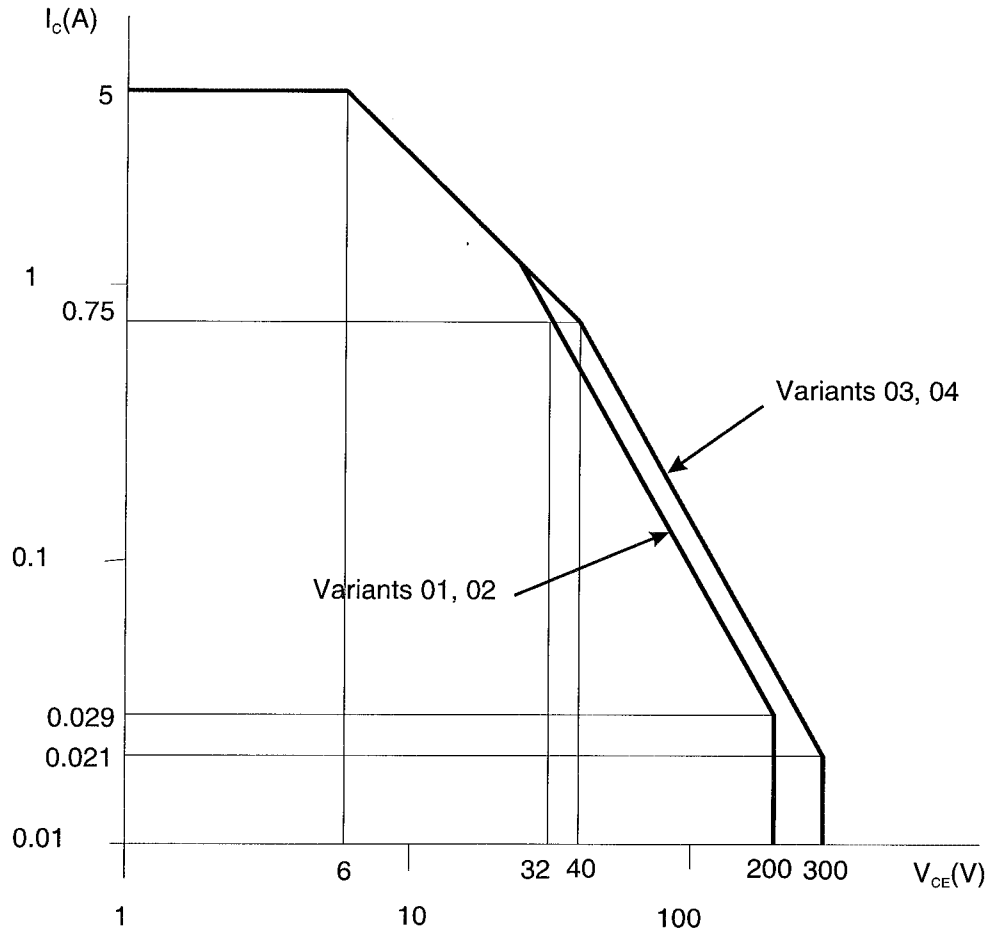
NOTES:

- 1. For $T_{case} > +100^{\circ}C$, derate linearly to 0W at $+200^{\circ}C$.
- 2. For Variants with tin-lead plating or hot solder dip lead finish all testing performed at $T_{amb} > +125^{\circ}C$

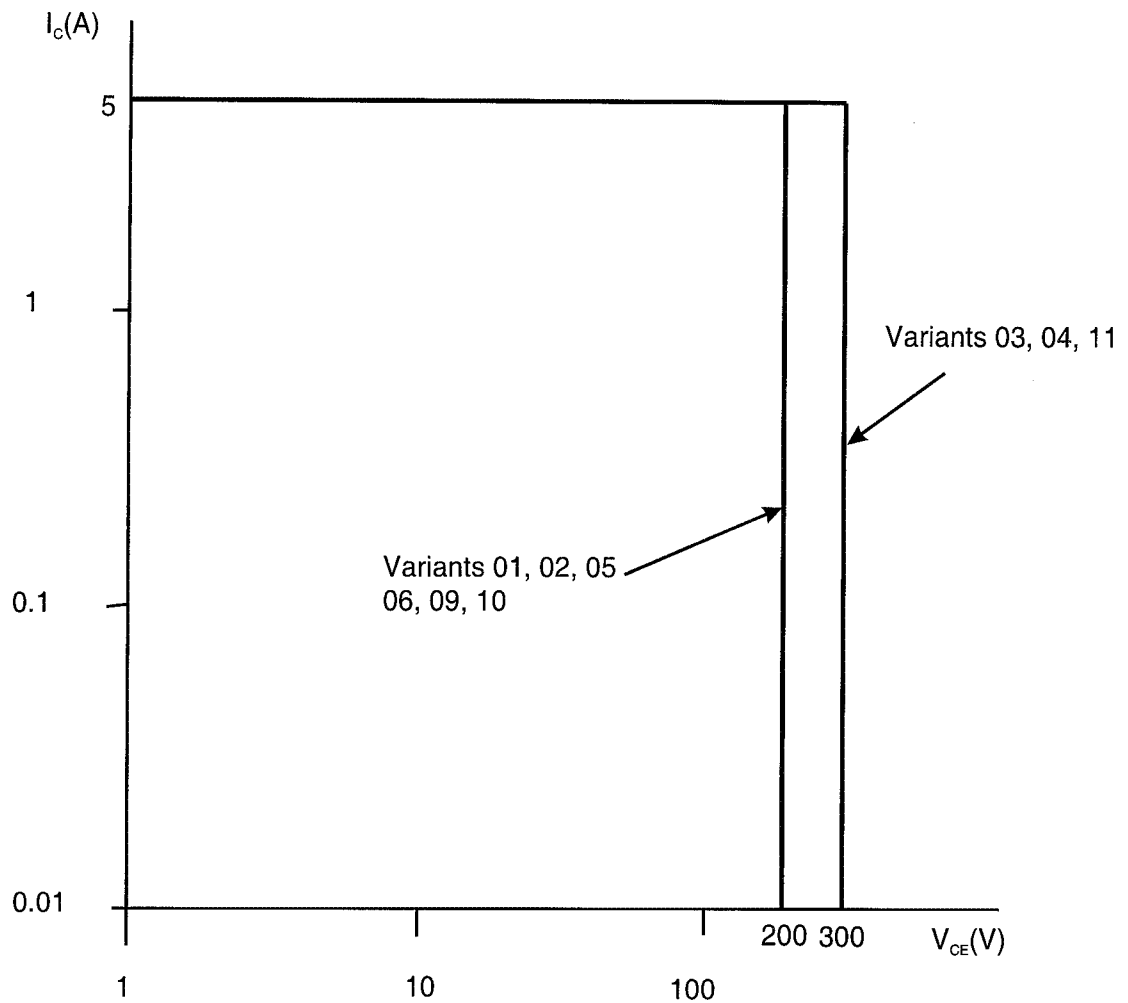
Power Dissipation For TO-66 For TO-5 and TO-39	P_{tot1}	2.5 1.2	W	At $T_{amb} \leq +25^{\circ}\text{C}$
	P_{tot2}	30 15	W	At $T_{case} \leq +100^{\circ}\text{C}$
Thermal Resistance, Junction-to-Ambient For TO-66 For TO-5 and TO-39	$R_{th(j-a)}$	70 145.8	$^{\circ}\text{C}/\text{W}$	
Thermal Resistance, Junction-to-Case For TO-66 For TO-5 and TO-39	$R_{th(j-c)}$	3.3 6.7	$^{\circ}\text{C}/\text{W}$	

2. shall be carried out in a 100% inert atmosphere.
 Safe Operating Area applies as follows:

Maximum Safe Operating Area Graph (Continuous DC) for Variants 01 to 04



Maximum Safe Operating Area Graph (Continuous DC) for Variants 05, 06, 09, 10 and 11



3. ✖ Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

1.6

PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

Consolidated notes are given following the case drawings and dimensions.